



INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-022	Serial No. 10/003,358-4650
	Applicant CHANG, Fang-Cheng	
	Filing Date 11/14/2001	Group 2151 2825

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
JSA	5,326,659	7/5/1994	Liu, et al.	430	5	3/5/1992
	5,572,598	11/5/1996	Wihl, et al.	382	144	2/25/1994
	5,795,688	8/18/1998	Burdorf, et al.	430	30	8/14/1996
	5,804,340	9/8/1998	Garza, et al.	430	5	12/23/1996
	5,849,440	12/15/1998	Lucase, et al.	430	5	1/29/1997
	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
	6,023,328	2/8/2000	Pierrat	237.4	2/23/1998	
	6,076,465	6/20/2000	Vacca, et al.	101	481	9/19/1997
	6,078,738	6/20/2000	Garza, et al.	395	500.22	5/8/1997
	6,091,845	7/18/2000	Pierrat, et al.	382	144	2/24/1998
	6,272,236	8/7/2001	Pierrat, et al.	382	144	7/18/2000
	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999
	6,334,209 B1	12/25/2001	Hashimoto, et al.	716	21	9/2/1999
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998
JSA	2002/0035461 A1	3/21/2002	Chang, et al.	703	13	7/16/2001

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SHEET 2 of 6

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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<u>JSR</u>	WO 00/36525 A2	6/22/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 97/13370	4/10/1997	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 98/20327	5/14/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 98/45685	10/15/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/38002	7/29/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/56113	11/4/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/59200	11/18/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/67626	12/29/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>
<u>JSR</u>	WO 99/14706 A2/A3	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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James Puntis

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	Filing Date 11/14/2001	

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EXAMINER'S INITIALS	CITATION
<i>JSA</i>	Spence, C., et al., "Detection of 60(degree) Phase Defects on Alternating PSMs", Advanced Micro Devices, KLA-Tencor, DuPont RTC (2 pages).
	Stimiman, J., et al., "Spatial Filter Models to Describe IC Lithographic Behavior". Precim Corporation, Portland, Oregon (10 pages).
	Sugawara, M., et al., "Defect Printability Study of Attenuated Phase-Shifting Masks for Specifying Inspection Sensitivity", Sony Corporation, Kanagawa, Japan (16 pages).
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	Adam, K., et al., "Simplified Models for Edge Transitions in Rigorous Mask Modeling", University of California Berkeley (40 pages).
	Gordon, R., et al., "Mask Topography Simulation for EUV Lithography", FINLE Technologies Inc. (15 pages).
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	Erdmann, A., "Topography Effects and Wave Aberrations in Advanced PSM-Technology", Fraunhofer Institute of Integrated Circuits (11 pages).
	Fiekowsky, P., "The End of Thresholds: Subwavelength Optical Linewidth Measurement Using the Flux-Area Technique", Automated Visual Inspection (6 pages).
<i>JSA</i>	Neureuther, A., et al., "Modeling Defect-Feature Interactions in the Presence of Aberrations", University of California Berkeley (10 pages).

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James Sun Lin

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<i>JFA</i>	Mathur, B.P., et al., "Quantitative Evaluation of Shape of Image on Photoresist of Square Apertures", IEEE, Transactions On Electron Devices, Vol. 35, No. 3, pp. 294-297, March 1988.		
	Neureuther, A., "Modeling Phase Shifting Masks", SPIE, 10th Annual Symposium On Microlithography, Vol. 1496, pp. 80-85 (1990).		
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	Ohtsuka, H., et al., "Evaluation of Repair Phase and Size Tolerance for a Phase-Shift Mask", J. Vac. Sci. Technol. B, Vol. 11, No. 6, pp. 2665-2668, November/December 1993.		
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EXAMINER'S INITIALS	CITATION		
JSL	Wiley, J., et al., "The Effect of Off-Axis Illumination on the Printability of Opaque and Transparent Reticle Defects", SPIE, Vol. 2512, pp. 432-440 (1995).		
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JSL	Balasinski, A., et al., "A Novel Approach to Simulate the Effect of Optical Proximity on MOSFET Parametric Yield", IEEE, pp. 37.6.1-37.6.4 (1999).		

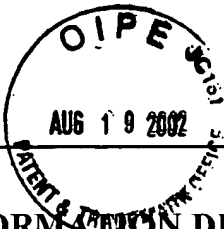
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James Pan & Co.

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<i>JSA</i>	Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).	
<i>JSA</i>	Fiekowsky, P., et al., "Defect Printability Measurement on the KLA-351: Correlation to Defect Sizing Using the AVI Metrology System", SPIE 19th Annual BACUS Symposium on Photomask Technology and Management Conference, pp. 1-6, September 1999.	
<i>JSA</i>	Tejnil, E., et al., "Option for At-Wavelength Inspection of Patterned Extreme Ultraviolet Lithography Masks", SPIE Bacus '99, pp. 1-12 (1999).	
<i>JSA</i>	Hemar, S., et al., "Finding Killer CD Variations by Full-Reticle CD Mapping", Microlithography World, pp. 4, 6, 8 & 10 (Summer 2000).	

EXAMINER: *James P. Smith*Date Considered: 7-26-04

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